

STF92

SMALL SIGNAL PNP TRANSISTOR

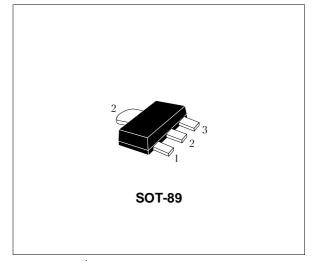
PRELIMINARY DATA

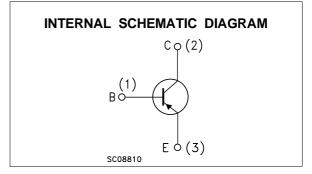
Туре	Marking
STF92	692

- SILICON EPITAXIAL PLANAR PNP HIGH VOLTAGE TRANSISTOR
- MINIATURE SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS STF42

APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage $(I_E = 0)$	-300	V	
V_{CEO}	Collector-Emitter Voltage $(I_B = 0)$	-300	V	
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	-5	V	
lc	Collector Current	-0.1	A	
Ісм	Collector Peak Current	-0.2	A	
P _{tot}	Total Dissipation at $T_C = 25 \ ^{\circ}C$	1.3	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

May 2002

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Мах	96.1	°C/W
 Device mour 	ted on a PCB area of 1 cm ²			

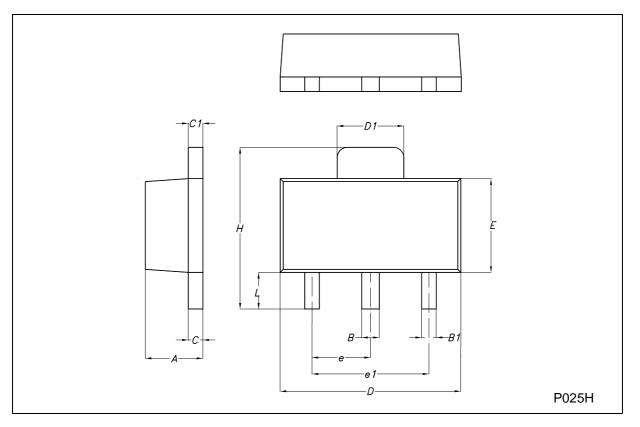
ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)				-10 -10 -100	nΑ μΑ μΑ
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = -5 V			-50	nA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-300			V
V(br)ceo*	Collector-Emitter Breakdown Voltage (I _B = 0)	Ic = -10 mA	-300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -100 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = -30 mA $I_{\rm B}$ = -5 mA			-0.6	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_{\rm C} = -30 \text{ mA}$ $I_{\rm B} = -5 \text{ mA}$			-1.2	V
h _{FE} *	DC Current Gain	$I_{C} = -30 \text{ mA}$ $V_{CE} = -10 \text{ V}$	75			
f⊤	Transition Frequency	$I_{C} = -15mA$ $V_{CE} = -10V$ f = 20 MHz	60			MHz
Ссво	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = -10 V f = 1 MHz$		6		pF
Cebo	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = -2 V f = 1 MHz$		22		pF

* Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1.5 %

DIM.		mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	1.4		1.6	55.1		63.0	
В	0.44		0.56	17.3		22.0	
B1	0.36		0.48	14.2		18.9	
С	0.35		0.44	13.8		17.3	
C1	0.35		0.44	13.8		17.3	
D	4.4		4.6	173.2		181.1	
D1	1.62		1.83	63.8		72.0	
E	2.29		2.6	90.2		102.4	
е	1.42		1.57	55.9		61.8	
e1	2.92		3.07	115.0		120.9	
Н	3.94		4.25	155.1		167.3	
L	0.89		1.2	35.0		47.2	





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